

ABSTRACT

A semiconductor memory device includes a memory cell array in which memory cells each having six transistors 11a, 11b, 12a, 12b, 13a and 13b are arranged two-dimensionally on a semiconductor substrate. The semiconductor

5 memory device also includes a plurality of word lines connected to each of the memory cells, and arranged on a parallel to each other along a first direction, a plurality of bit lines connected to each of the memory cells and arranged on a parallel to each other along a second direction perpendicular to the first direction, and at least two gate electrodes provided on the semiconductor substrate such

10 that each of the gate electrodes is connected to at least one transistor of the six transistors, all of the gate electrodes 3a, 3b, 3c and 3d being arranged on the same straight line parallel to the first direction.